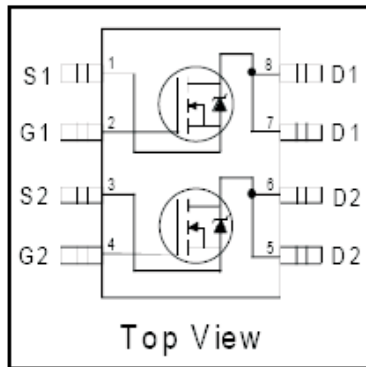
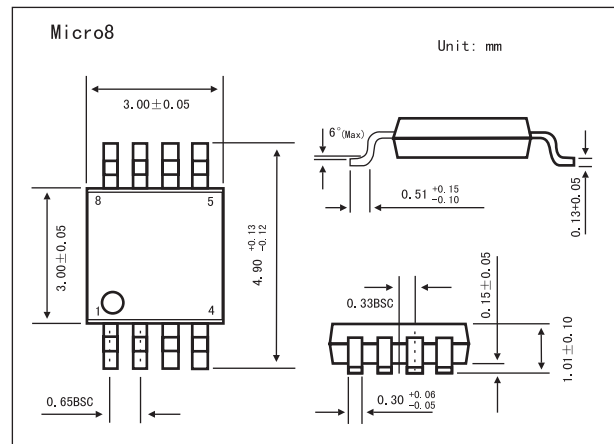


HEXFET[®] Power MOSFET

KRF7503

■ Features

- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape & Reel
- Fast Switching



■ Absolute Maximum Ratings Ta = 25°C


Parameter	Symbol	Rating	Unit
Continuous Drain Current, V _{GS} @ 10V, Ta = 25°C	I _D	2.4	A
Continuous Drain Current, V _{GS} @ 10V, Ta = 70°C	I _D	1.9	
Pulsed Drain Current*1	I _{DM}	14	
Power Dissipation Ta = 25°C *1	P _D	1.25	W
Linear Derating Factor		10	mW/°C
Gate-to-Source Voltage	V _{GS}	±12	V
Peak Diode Recovery dv/dt*1	dv/dt	5	V/ns
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C
Junction-to-Ambient *2	R _{θJA}	100	°C/W

* I_{SD} ≤ 1.7A, di/dt ≤ 120A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C

*2 Surface mounted on FR-4 board, t ≤ 10sec.

KRF7503

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250 \mu A$	30			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1mA, \text{Reference to } 25^\circ C$		0.059		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.7A^{*1}$			0.135	Ω
		$V_{GS} = 4.5V, I_D = 0.85A^{*1}$			0.222	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0			V
Forward Transconductance	g_{fs}	$V_{DS} = 10V, I_D = 0.85A^{*1}$	1.9			S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1.0	μA
		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ C$			25	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = -20V$			-100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = 20V$			100	
Total Gate Charge	Q_g	$I_D = 1.7A$		7.8	12	nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = 24V$		1.2	1.8	
Gate-to-Drain ("Miller") Charge	Q_{gd}	$V_{GS} = 10V,^{*1}$		2.5	3.8	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15V$		4.7		ns
Rise Time	t_r	$I_D = 1.7A$		10		
Turn-Off Delay Time	$t_{d(off)}$	$R_G = 6.0 \Omega$		12		
Fall Time	t_f	$R_D = 8.7 \Omega$		5.3		
Input Capacitance	C_{iss}	$V_{GS} = 0V$		210		pF
Output Capacitance	C_{oss}	$V_{DS} = 25V$		80		
Reverse Transfer Capacitance	C_{rss}	$f = 1.0MHz$		32		
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 			1.25	A
Pulsed Source Current (Body Diode) *2	I_{SM}				14	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = 1.7A, V_{GS} = 0V^{*1}$			1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = 1.7A, V_R = 10V$		40	60	ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s^{*1}$		48	72	nC

*1 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

*2 Repetitive rating; pulse width limited by max